

Amendments to the claims

The following replaces all prior versions of the claims:

- 1 – 6. (Cancelled)
7. (Currently Amended) The manufacturing process for a silicon epitaxial wafer according to claim 622, wherein the interstitial oxygen concentration is in a range of from $6 \times 10^{17}/\text{cm}^3$ to $10 \times 10^{17}/\text{cm}^3$.
8. (Currently Amended) The manufacturing process for a silicon epitaxial wafer according to claim 622, wherein the heat treatment temperature is in a range of from 500°C to 700°C .
9. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 7, wherein the heat treatment temperature is in a range of from 500°C to 700°C .
- 10-13. (Cancelled)
14. (Currently Amended) The manufacturing process for a silicon epitaxial wafer according to claim 622, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.
15. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 7, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.
16. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 8, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.

17. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 9, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.

18-21. (Cancelled)

22. (New) A manufacturing process for a silicon epitaxial wafer comprising the steps of:

providing a silicon substrate with an interstitial oxygen concentration in a range of from $4 \times 10^{17}/\text{cm}^3$ to $10 \times 10^{17}/\text{cm}^3$ and a substrate resistivity of $0.02 \Omega\text{-cm}$ or lower;

forming an epitaxial layer over the silicon substrate at a temperature of 1000°C or higher to obtain the silicon epitaxial wafer, whereby the interstitial oxygen concentration of the silicon substrate is decreased; and

forming new oxygen precipitation nuclei and increasing bulk defect density of the silicon substrate without reducing internal gettering by applying heat treatment to the silicon epitaxial wafer at a temperature in a range of from 450°C to 750°C , whereby the new oxygen precipitation nuclei are uniformly formed in the substrate.